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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/619,479	07/19/2000	Shunpei Yamazaki	0756-2188	1883

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NIXON PEABODY, LLP
8180 GREENSBORO DRIVE
SUITE 800
MCLEAN, VA 22102

EXAMINER

RUDE, TIMOTHY L

ART UNIT	PAPER NUMBER
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2871

DATE MAILED: 03/28/2002

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Applicati n N .

09/619,479

Applicant(s)

YAMAZAKI ET AL.

Examiner

Timothy L Rude

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 19 July 2000.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-22 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-22 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on _____ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

- 13) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☒ All b) ☐ Some * c) ☐ None of:
1. ☒ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☒ Information Disclosure Statement(s) (PTO-1449) Paper No(s) 4.
- 4) ☐ Interview Summary (PTO-413) Paper No(s). _____.
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____.

DETAILED ACTION

Claim Objections

1. Claim 15 is objected to because of the following informalities: The recitation, "wherein said active device and said pixel electrode and said photo-electric conversion device are provided in one of pixels arranged in matrix," is repeated. For examination purposes, the second recitation will be disregarded. Appropriate correction is required.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

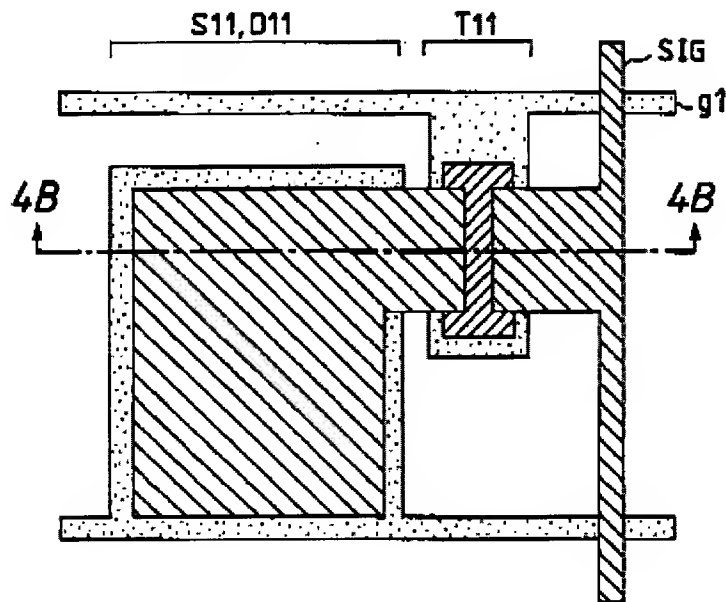
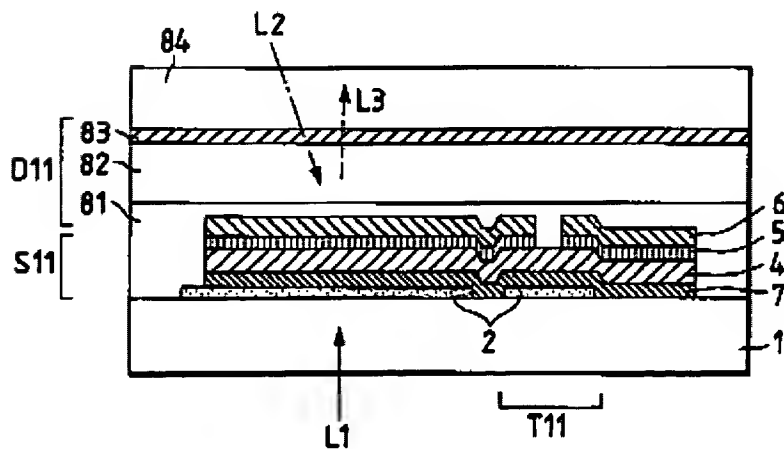
(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

2. Claims 1, 2, 8, 10-13, 19, 21, and 22 are rejected under 35 U.S.C. 102(b) as being anticipated by Kaifu et al (Kaifu) USPAT 5,812,109.

As to claim 1, Kaifu discloses in Figures 3, 4A, and 4B, an integral image recognition/display apparatus comprising: a plurality of pixel portions, D11, each having an active device, T11, and arranged in matrix and each having a pixel electrode, 2 (left portion in Figure 4B), comprising a reflecting material, 6, and a light-transmitting material, 81, over an active matrix substrate, 1; and a plurality of sensor portions, S11, arranged in matrix over said active matrix substrate, wherein said sensor portion includes a photo-electric conversion device, 4, and can read information by utilizing the

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rays of light transmitting through said light-transmitting material when an external image is read (Abstract).

FIG. 4A**FIG. 4B**

Note: the removal (col. 7, lines 12-22) of a portion of the aluminum electrode, 6, is not shown in Figures 4A and 4B. However, an illustration may be found in Figures 11A and 11B.

FIG. 11A

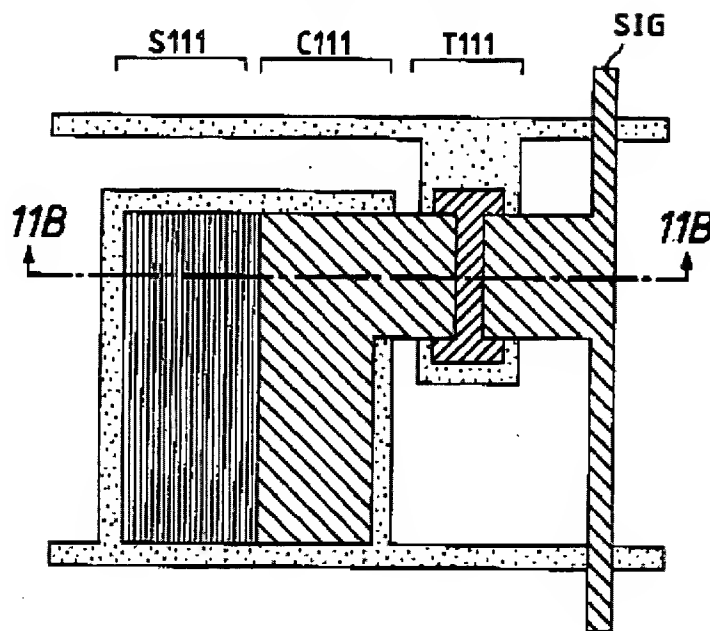
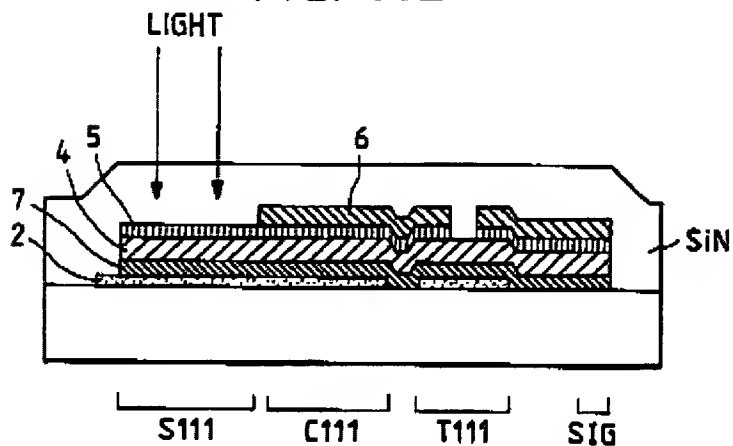


FIG. 11B



As to claim 2, Kaifu discloses in Figure 4B the apparatus according to claim 1, wherein said active device comprises a bottom gate type TFT, T11.

As to claim 8, Kaifu discloses in Figures 3, 4A, and 4B, an integral image recognition/display apparatus comprising: a plurality of pixel portions, D11, each having an active device, T11, and arranged in matrix and each having a pixel electrode, (left portion in Figure 4B), comprising a reflecting material, 6, and a light-transmitting material, 5, over an active matrix substrate, 1; and a plurality of sensor portions, S11, arranged in matrix over said active matrix substrate, wherein said sensor portion has a photo-electric conversion device, 4, and at least a part of said photo-electric conversion device, 4, is extended in such a manner as to overlap with said active device, T11.

As to claim 10, Kaifu discloses in Figure 4B an integral image recognition/display apparatus comprising: a plurality of pixel portions, D11, each having an active device, T11, and arranged in matrix over an active matrix substrate, 1; and a plurality of sensor portions, S11, arranged in matrix over said active matrix substrate, wherein a pixel capacitance portion (electrodes 2 and 6) provided to each of said pixel portions functions also as a capacitance portion for image recognition, disposed in corresponding one of said sensor portions (col. 7, line 44 through col. 10, line 38).

As to claim 11, Kaifu discloses in Figures 3, 4A, and 4B, an apparatus according to claim 10, wherein a reflecting material, 6, and a light-transmitting material, 5, are used for a pixel electrode of each of said pixel portions.

As to claim 12, Kaifu discloses in Figures 3, 4A, and 4B, a semiconductor device comprising: a pixel portion, D11, having an active device, T11, and a pixel electrode comprising a reflecting material, 6, and a light-transmitting material, 5, over an active matrix substrate; and a sensor portion, S11, provided over said active matrix substrate, 1; and comprising a photo-electric conversion device, 4, wherein said active device and said pixel electrode and said photo-electric conversion device are provided in one of pixels arranged in matrix, and wherein said sensor portion can read information by utilizing the rays of light transmitting through said light-transmitting material when an external image is read (Abstract).

As to claim 13, Kaifu discloses in Figure 4B the apparatus according to claim 12, wherein said active device comprises a bottom gate type TFT, T11.

As to claim 19, Kaifu discloses in Figures 3, 4A, and 4B, a semiconductor device comprising: a pixel portion, D11, having an active device, T11, and a pixel electrode comprising a reflecting material, 6, and a light-transmitting material, 5, over an active matrix substrate, 1; and a sensor portion, S11, provided over said active matrix substrate and having a photo-electric conversion device, 4, wherein said active device and said pixel electrode and said photo-electric conversion device are provided in one of pixels arranged in matrix, and wherein at least a part of said photo-electric conversion device, 4, is extended in such a manner as to overlap with said active device, T11.

As to claim 21, Kaifu discloses in Figure 4B a semiconductor device comprising: a pixel portion, D11, having an active device, T11, provided over an active matrix substrate, 1; and a sensor portion, S11, provided over said active matrix substrate, wherein a pixel capacitance portion (electrodes 2 and 6) provided to said pixel portion functions also as a capacitance portion for image recognition (col. 7, line 44 through col. 10, line 38), disposed in said sensor portion.

As to claim 22, Kaifu discloses in Figures 3, 4A, and 4B, an apparatus according to claim 21, wherein a reflecting material, 6, and a light-transmitting material, 5, are used for a pixel electrode of said pixel portion.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

3. Claims 3-7, 9, 14-18, and 20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kaifu in view of Itoh et al (Itoh) USPAT 5,585,817.

As to claim 3, Kaifu discloses the apparatus according to claim 1.

Kaifu does not explicitly disclose the use of a top gate type TFT.

Itoh teaches the use of a top gate TFT, 101, in an integral image recognition/display apparatus in Figure 1.

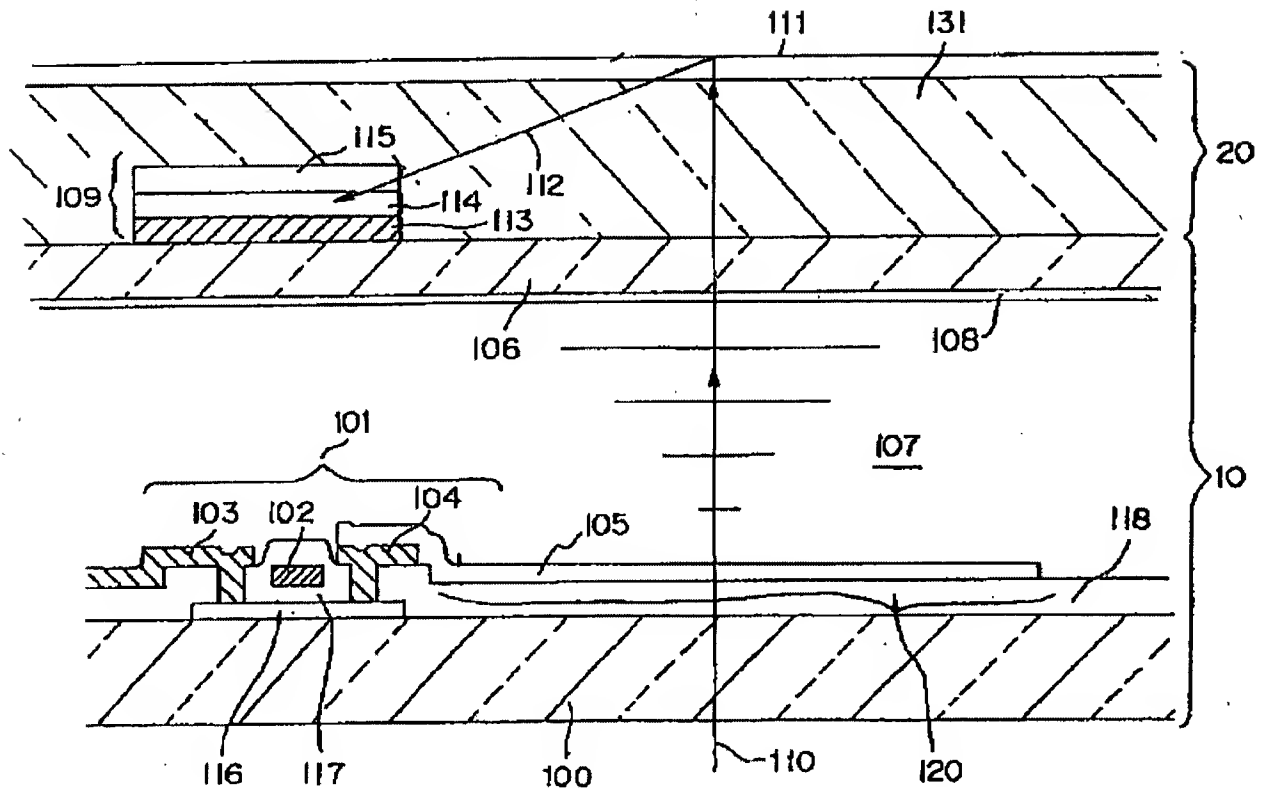


FIG. 1

Itoh is evidence that ordinary workers in the art of liquid crystals would find the reason, suggestion, or motivation to add top gate TFTs to drive the pixels of the display.

Therefore, it would have been obvious to one having ordinary skill in the art of liquid crystals at the time the invention was made to modify the integral image recognition/display apparatus of Kaifu with the top gate TFTs of Itoh.

As to claim 4, Kaifu discloses in Figures 3, 4A, and 4B, an integral image recognition/display apparatus comprising: a plurality of pixel portions, D11, each having an active device, T11, and arranged in matrix and each having a pixel electrode, 2 (left portion in Figure 4B), comprising a reflecting material, 6, and a light-transmitting material, 81, over an active matrix substrate, 1.

Kaifu does not explicitly disclose a plurality of sensor portions disposed in matrix over an opposed substrate constituting a display panel, wherein said sensor portion has a photo-electric conversion device, and can read information by utilizing the rays of light transmitting through said light-transmitting material when an external image is read.

Itoh teaches in Figure 1 the use of a plurality of sensor portions, 109, disposed in matrix over an opposed substrate, 106, constituting a display panel, wherein said sensor portion has a photo-electric conversion device (col. 4, lines 36-42), and can read information by utilizing the rays of light, 110, transmitting through said light-transmitting material when an external image, 111, is read.

Itoh is evidence that ordinary workers in the art of liquid crystals would find the reason, suggestion, or motivation to add photo-electric conversion devices to the opposed substrate to improve contrast (col. 4, lines 56-60).

Therefore, it would have been obvious to one having ordinary skill in the art of liquid crystals at the time the invention was made to modify the integral image recognition/display apparatus of Kaifu with photo-electric conversion devices on the opposed substrate of Itoh.

As to claim 5, Kaifu discloses the invention of a full color device (col. 19, lines 41-47).

Kaifu in view of Itoh does not explicitly disclose color filters disposed on the opposed substrate. However, the use of color filters on the opposed substrate is one of the most common configurations in the art of liquid crystals to simplify manufacture.

Kaifu is evidence that ordinary workers in the art of liquid crystals would find the reason, suggestion, or motivation to add color filters to the opposed substrate to facilitate a full color display.

Therefore, it would have been obvious to one having ordinary skill in the art of liquid crystals at the time the invention was made to modify the integral image recognition/display apparatus of Kaifu in view of Itoh with the color filters of Kaifu.

As to claim 6, Kaifu discloses in Figure 4B the use of a bottom gate type TFT, T11.

As to claims 7, 9, and 14, Itoh discloses in Figure 1 the use of a top gate type TFT, 101, to drive the pixel electrode. Furthermore, mere selection of top gate vs bottom gate type TFT is not considered patentably distinct. If Applicant does not agree, a restriction might be appropriate.

As to claim 15, Kaifu discloses in Figures 3, 4A, and 4B, a semiconductor device comprising: an active matrix substrate, 1, and an opposed substrate, 84; a pixel portion

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having an active device, T11, and a pixel electrode comprising a reflecting material, 6, and a light-transmitting material, 5, over said active matrix substrate.

Kaifu does not explicitly disclose a sensor portion provided over said opposed substrate and comprising a photo-electric conversion device, wherein said active device and said pixel electrode and said photo-electric conversion device are provided in one of pixels arranged in matrix, (*wherein said active device and said pixel electrode and said photo-electric conversion device are provided in one of pixels arranged in matrix,*) and wherein said sensor portion can read information by utilizing the rays of light transmitting through said light-transmitting material when an external image is read.

Itoh teaches in Figure 1 the use of a plurality of sensor portions, 109, disposed in matrix over an opposed substrate, 106, constituting a display panel, wherein said sensor portion has a photo-electric conversion device (col. 4, lines 36-42), and can read information by utilizing the rays of light, 110, transmitting through said light-transmitting material when an external image, 111, is read.

Itoh is evidence that ordinary workers in the art of liquid crystals would find the reason, suggestion, or motivation to add photo-electric conversion devices to the opposed substrate to improve contrast (col. 4, lines 56-60).

Therefore, it would have been obvious to one having ordinary skill in the art of liquid crystals at the time the invention was made to modify the integral image recognition/display apparatus of Kaifu with photo-electric conversion devices on the opposed substrate of Itoh.

As to claim 16, Kaifu discloses the invention of a full color device (col. 19, lines 41-47).

Kaifu in view of Itoh does not explicitly disclose color filters disposed on the opposed substrate. However, the use of color filters on the opposed substrate is one of the most common configurations in the art of liquid crystals to simplify manufacture.

Kaifu is evidence that ordinary workers in the art of liquid crystals would find the reason, suggestion, or motivation to add color filters to the opposed substrate to facilitate a full color display.

Therefore, it would have been obvious to one having ordinary skill in the art of liquid crystals at the time the invention was made to modify the integral image recognition/display apparatus of Kaifu in view of Itoh with the color filters of Kaifu.

As to claim 17, Kaifu discloses in Figure 4B the use of a bottom gate type TFT, T11.

As to claims 18 and 20, Itoh discloses in Figure 1 the use of a top gate type TFT, 101, to drive the pixel electrode. Furthermore, mere selection of top gate vs bottom gate type TFT is not considered patentably distinct. If Applicant does not agree, a restriction might be appropriate.

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4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Timothy L Rude whose telephone number is (703) 305-0418. The examiner can normally be reached on Monday through Thursday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, William L Sikes can be reached on (703) 308-4842. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7724 for regular communications and (703) 308-7725 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 305-4900.



TLR
March 21, 2002

Timothy L Rude
Examiner
Art Unit 2871



William L. Sikes
Supervisory Patent Examiner
Technology Center 2800